

International IR Rectifier

- Ultra Low On-Resistance
- P-Channel MOSFET
- SOT-23 Footprint
- Low Profile (<1.1mm)
- Available in Tape and Reel
- Fast Switching
- 1.8V Gate Rated
- Lead-Free

Description

These P-Channel MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET® power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in battery and load management.

A thermally enhanced large pad leadframe has been incorporated into the standard SOT-23 package to produce a HEXFET Power MOSFET with the industry's smallest footprint. This package, dubbed the Micro3™, is ideal for applications where printed circuit board space is at a premium. The low profile (<1.1mm) of the Micro3 allows it to fit easily into extremely thin application environments such as portable electronics and PCMCIA cards. The thermal resistance and power dissipation are the best available.

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	-12	V
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -4.5\text{V}$	-4.3	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ -4.5\text{V}$	-3.4	
I_{DM}	Pulsed Drain Current ①	-34	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation	1.3	W
$P_D @ T_A = 70^\circ\text{C}$	Power Dissipation	0.8	
	Linear Derating Factor	0.01	W/°C
E_{AS}	Single Pulse Avalanche Energy④	33	mJ
V_{GS}	Gate-to-Source Voltage	± 8.0	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

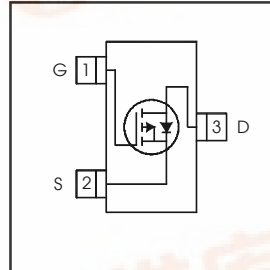
Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient③	75	100	°C/W

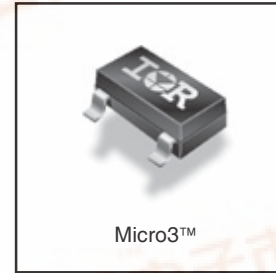
PD - 94891A

IRLML6401PbF

HEXFET® Power MOSFET



$V_{DS} = -12\text{V}$
 $R_{DS(on)} = 0.05\Omega$



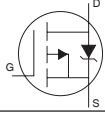
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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-12	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.007	—	V/°C	Reference to $25^\circ\text{C}, I_D = -1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.050	Ω	$V_{GS} = -4.5V, I_D = -4.3A$ ②
		—	—	0.085		$V_{GS} = -2.5V, I_D = -2.5A$ ②
		—	—	0.125		$V_{GS} = -1.8V, I_D = -2.0A$ ②
$V_{GS(th)}$	Gate Threshold Voltage	-0.40	-0.55	-0.95	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	Forward Transconductance	8.6	—	—	S	$V_{DS} = -10V, I_D = -4.3A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	$V_{DS} = -12V, V_{GS} = 0V$
		—	—	-25		$V_{DS} = -9.6V, V_{GS} = 0V, T_J = 55^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -8.0V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 8.0V$
Q_g	Total Gate Charge	—	10	15	nC	$I_D = -4.3A$
Q_{gs}	Gate-to-Source Charge	—	1.4	2.1		$V_{DS} = -10V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	2.6	3.9		$V_{GS} = -5.0V$ ②
$t_{d(on)}$	Turn-On Delay Time	—	11	—	ns	$V_{DD} = -6.0V$
t_r	Rise Time	—	32	—		$I_D = -1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	250	—		$R_D = 6.0\Omega$
t_f	Fall Time	—	210	—		$R_G = 89\Omega$ ②
C_{iss}	Input Capacitance	—	830	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	180	—		$V_{DS} = -10V$
C_{rss}	Reverse Transfer Capacitance	—	125	—		$f = 1.0\text{MHz}$

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-1.3	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-34		
V_{SD}	Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}, I_S = -1.3A, V_{GS} = 0V$ ②
t_{rr}	Reverse Recovery Time	—	22	33	ns	$T_J = 25^\circ\text{C}, I_F = -1.3A$
Q_{rr}	Reverse Recovery Charge	—	8.0	12	nC	$di/dt = -100A/\mu s$ ②

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ③ Surface mounted on 1" square single layer 1oz. copper FR4 board, steady state.
- ④ Starting $T_J = 25^\circ\text{C}, L = 3.5\text{mH}$
 $R_G = 25\Omega, I_{AS} = -4.3A$.

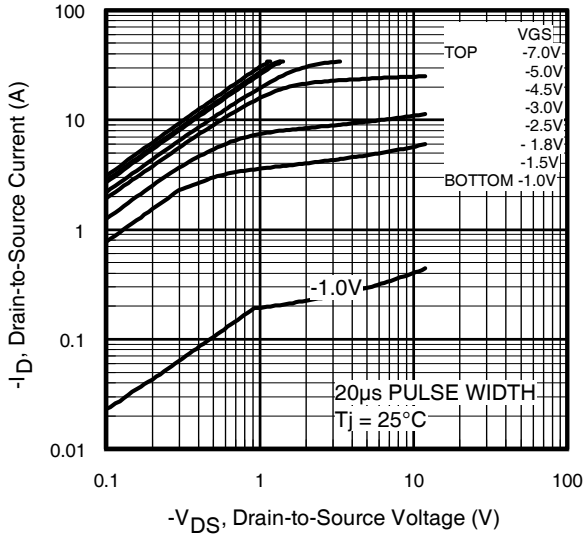


Fig 1. Typical Output Characteristics

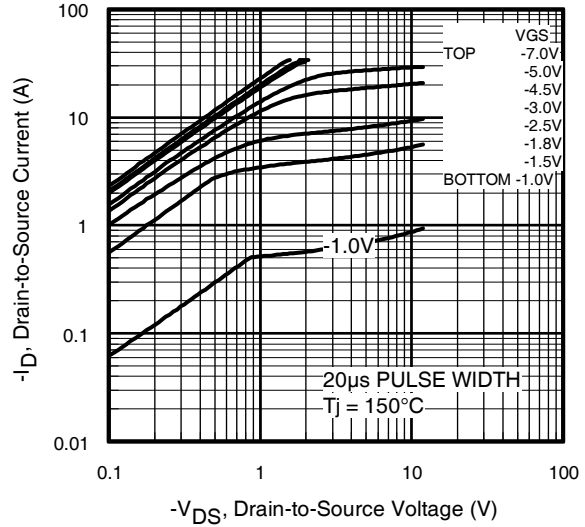


Fig 2. Typical Output Characteristics

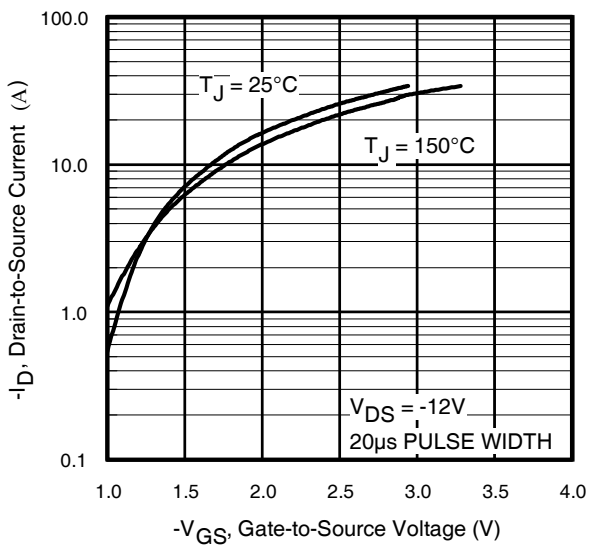


Fig 3. Typical Transfer Characteristics

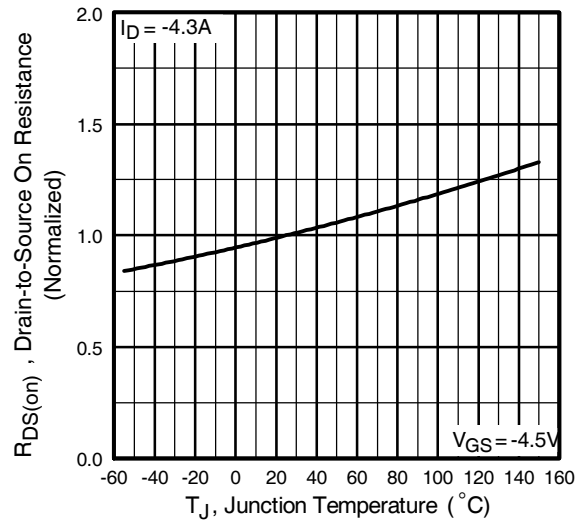


Fig 4. Normalized On-Resistance Vs. Temperature

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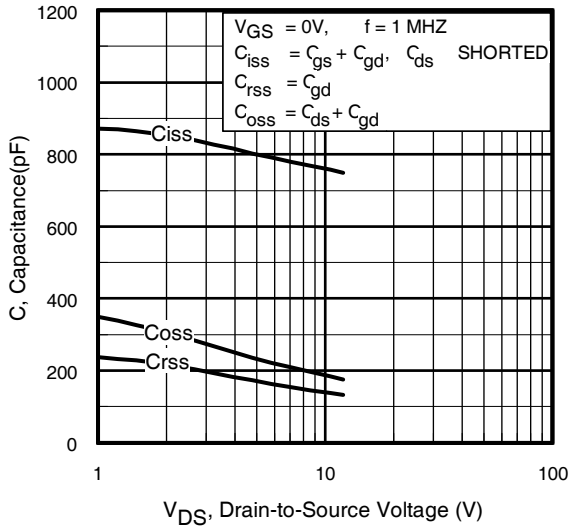


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

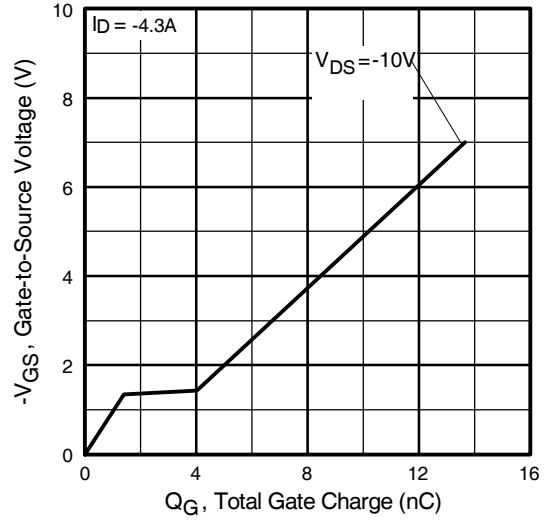


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

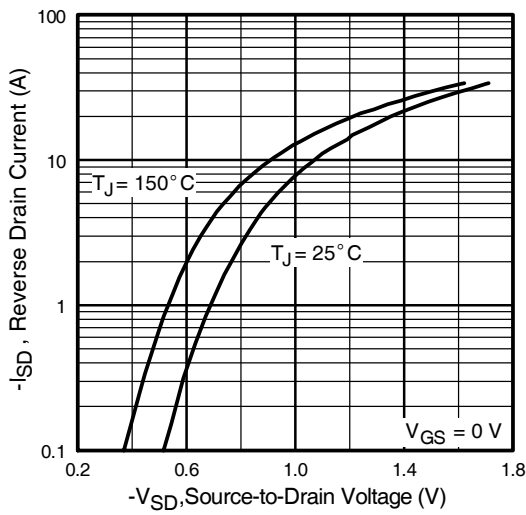


Fig 7. Typical Source-Drain Diode Forward Voltage

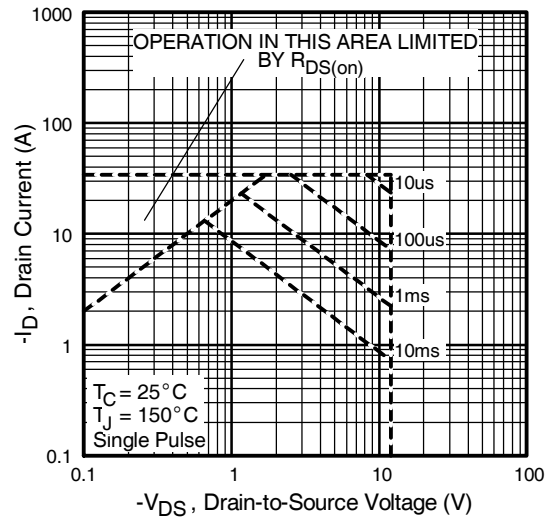


Fig 8. Maximum Safe Operating Area

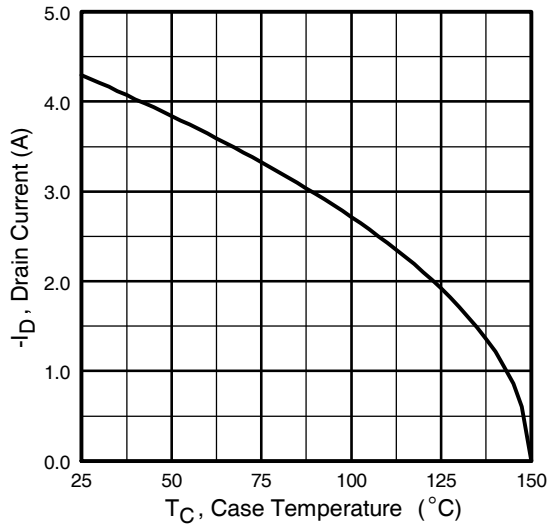


Fig 9. Maximum Drain Current Vs. Case Temperature

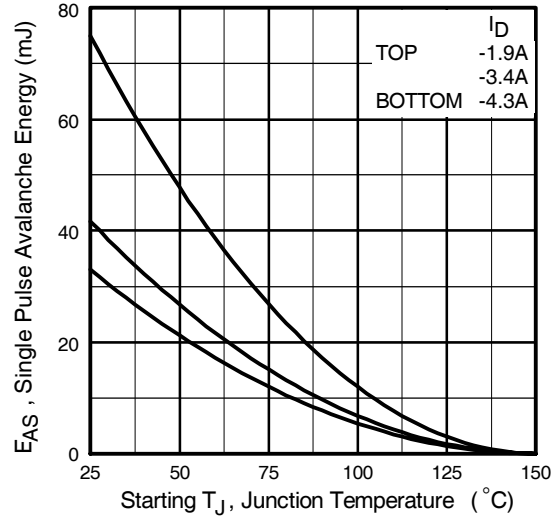


Fig 10. Maximum Avalanche Energy Vs. Drain Current

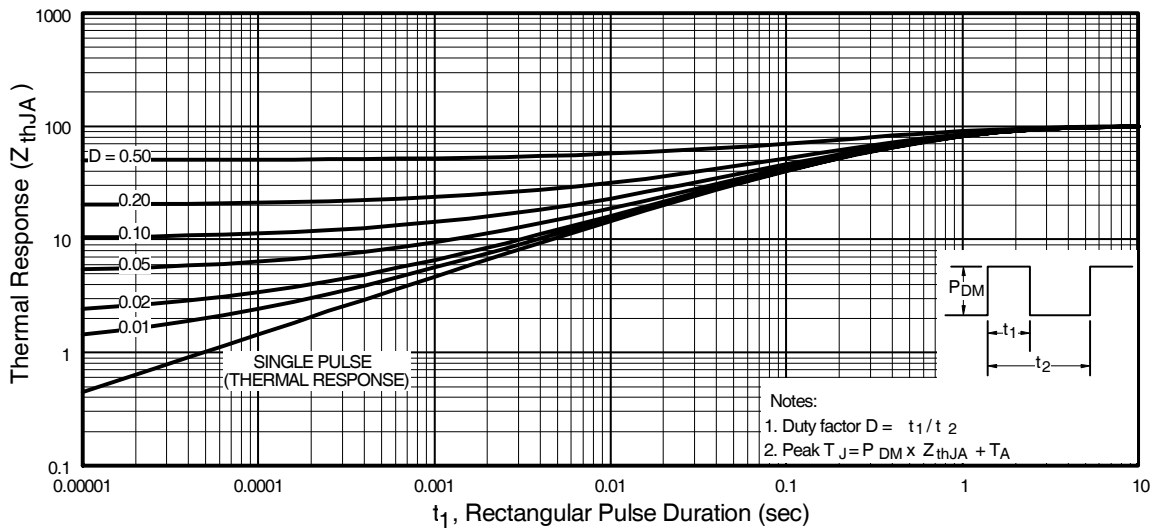


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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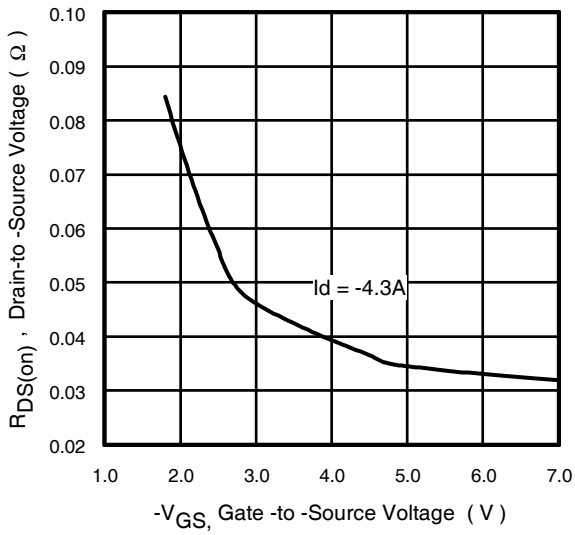


Fig 12. Typical On-Resistance Vs. Gate Voltage

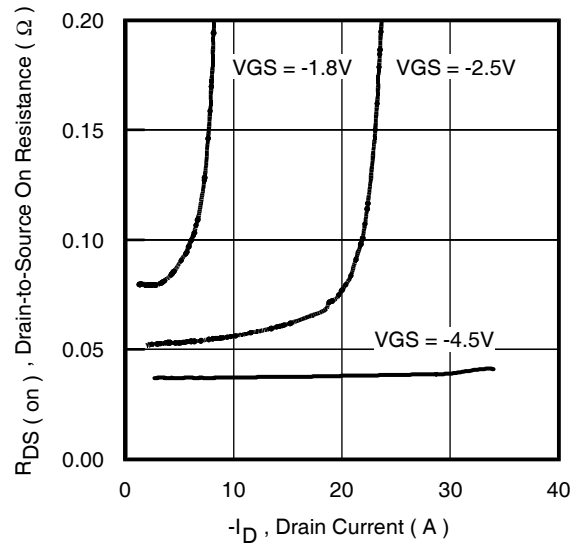


Fig 13. Typical On-Resistance Vs. Drain Current

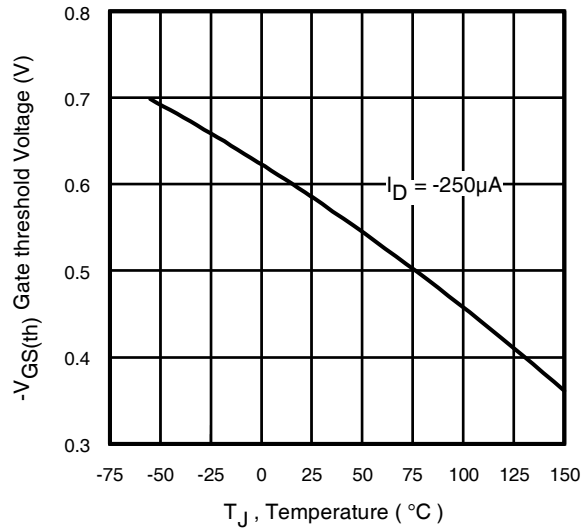
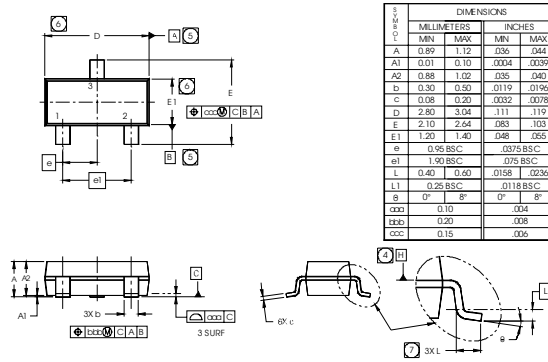


Fig 14. Typical Threshold Voltage Vs. Junction Temperature

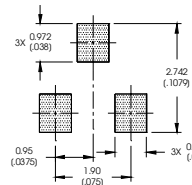
Micro3 (SOT-23) Package Outline

Dimensions are shown in millimeters (inches)



DIMENSION	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.89	1.12	.036	.044
A1	0.01	0.10	.004	.0039
A2	0.88	1.02	.035	.040
b	0.30	0.50	.0119	.0196
c	0.08	0.20	.0032	.0078
D	2.83	3.04	.111	.119
E	2.10	2.64	.083	.103
E1	1.20	1.40	.048	.055
e	0.95 BSC		.0375 BSC	
e1	1.90 BSC		.075 BSC	
L	0.40	0.60	.0158	.0236
L1	0.25 BSC		.0118 BSC	
B	0"	8"	0"	8"
HHH	0.10		.004	
HHK	0.20		.008	
CCC	0.15		.006	

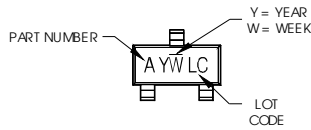
RECOMMENDED FOOT PRINT



- NOTES
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994.
 - DIMENSIONS ARE SHOWN IN MILLIMETERS AND INCHES.
 - CONTROLLING DIMENSION: MILLIMETER.
 - DATUM PLANE H IS LOCATED AT THE MOLD PARTING LINE.
 - DATUM A AND B TO BE DETERMINED AT DATUM PLANE H.
 - DIMENSIONS D AND E1 ARE MEASURED AT DATUM PLANE H.
 - DIMENSION L IS THE LEAD LENGTH FOR SOLDERING TO A SUBSTRATE.
 - CUTLINE CONFORMS TO JEDEC OUTLINE TO-236AB.

Micro3 (SOT-23/TO-236AB) Part Marking Information

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR



PART NUMBER CODE REFERENCE:

- A = IRLML2402
- B = IRLML2803
- C = IRLML6302
- D = IRLML5103
- E = IRLML6402
- F = IRLML6401
- G = IRLML2502
- H = IRLML5203

Note: A line above the work week (as shown here) indicates Lead-Free.

YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
1994	4	04	D
1995	5		
1996	6		
1997	7		
1998	8		
1999	9		
2000	0	24	X
		25	Y
		26	Z

W = (27-52) IF PRECEDED BY A LETTER

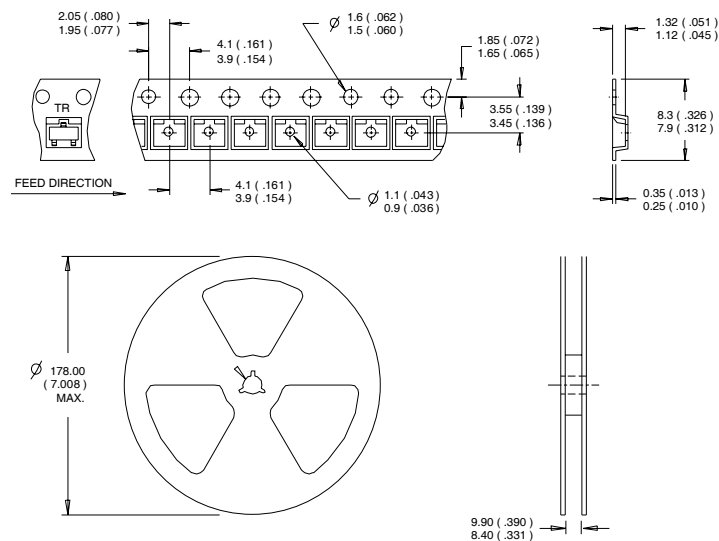
YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
1994	D	30	D
1995	E		
1996	F		
1997	G		
1998	H		
1999	J		
2000	K	50	X
		51	Y
		52	Z

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Micro3™ Tape & Reel Information

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.
This product has been designed and qualified for the consumer market.
Qualification Standards can be found on IR's Web site.

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Visit us at www.irf.com for sales contact information. 11/04